

HAT2208RJ-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)		
30	0.008 at V _{GS} = 10 V	13	6.1 nC		
30	0.011 at V _{GS} = 4.5 V	11	0.1110		

SO-8

Top View

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FEATURES

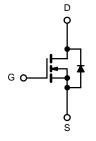
- · Halogen-free
- Trench Power MOSFET



- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

- Notebook CPU Core
 - High-Side Switch



N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	30	V		
Gate-Source Voltage	V_{GS}	± 20	V		
	T _C = 25 °C	I _D	13		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C		10		
Continuous Drain Current (1) = 130 C)	T _A = 25 °C		9 ^{b, c}		
	T _A = 70 °C		7 ^{b, c}	_	
Pulsed Drain Current	I _{DM}	45	Α		
Ocation and Ocaman Brain Binds Ocaman	T _C = 25 °C	1.	3.7		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.0 ^{b, c}		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20		
Avalanche Energy	L = 0.111111	E _{AS}	21	mJ	
	T _C = 25 °C	P _D	4.1	W	
Maximum Dayor Dissipation	T _C = 70 °C		2.5		
Maximum Power Dissipation	T _A = 25 °C		2,2 ^{b, c}		
	T _A = 70 °C		1.3 ^{b, c}		
Operating Junction and Storage Temperature Ra	T _J , T _{stq}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R_{thJA}	39	55	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	29]		

Notes:

- a. Base on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 10 s.
- d. Maximum under Steady State conditions is 85 °C/W.



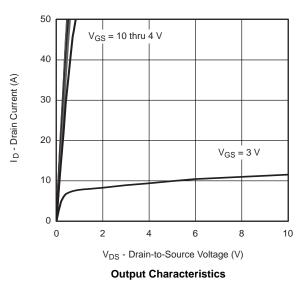
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static		,					
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		26		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_{J}$	I _D = 250 μA		- 6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1.0		3.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Oata Valla va Busia Oamaat		V _{DS} = 30 V, V _{GS} = 0 V			1	μА	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	10		10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
	_	V _{GS} = 10 V, I _D = 10 A	0.008				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 9 A		0.011		Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		50		S	
Dynamic ^b					l		
Input Capacitance	C _{iss}			800		pF	
Output Capacitance	C _{oss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		165			
Reverse Transfer Capacitance	C _{rss}			73			
Total Gate Charge	Q_g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A		15	23	nC	
				6.8	10.2		
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 10 \text{ A}$		2.5			
Gate-Drain Charge	Q_{gd}			2.3			
Gate Resistance	R_g	f = 1 MHz	0.36	1.8	3.6	Ω	
Turn-On Delay Time	t _{d(on)}			16	23		
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		12	16		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		16	22		
Fall Time	t _f			10	18]	
Turn-On Delay Time	t _{d(on)}			8	16	ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.4 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 9 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		16	22		
Fall Time	t _f			8	15		
Drain-Source Body Diode Characterist	ics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			10	^	
Pulse Diode Forward Current ^a	I _{SM}				50	A	
Body Diode Voltage	V_{SD}	I _S = 9 A		0.8	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns	
Body Diode Reverse Recovery Charge	$I_{\rm F} = 9 \text{A. dI/dt} = 100 \text{A/us.} I_{\rm T} = 25$			6	12	nC	
Reverse Recovery Fall Time				8			
Reverse Recovery Rise Time	t _b			7		ns	

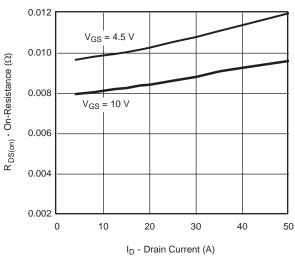
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

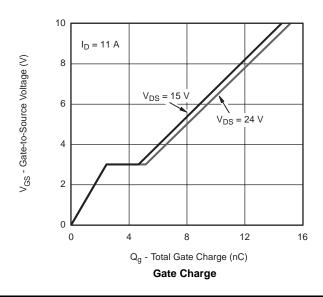
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



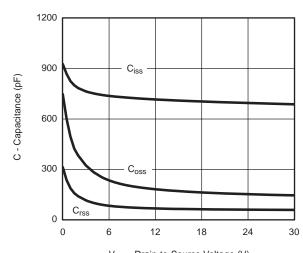




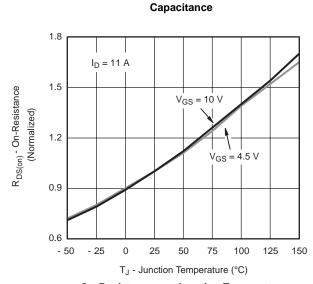
On-Resistance vs. Drain Current and Gate Voltage



V_{GS} - Gate-to-Source Voltage (V) **Transfer Characteristics**

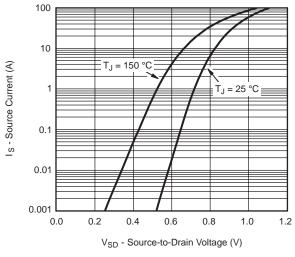


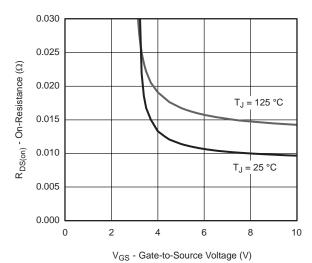
V_{DS} - Drain-to-Source Voltage (V)



On-Resistance vs. Junction Temperature

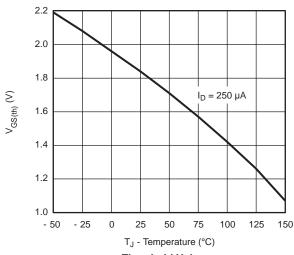


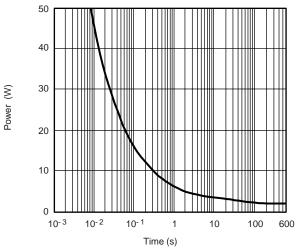




Source-Drain Diode Forward Voltage

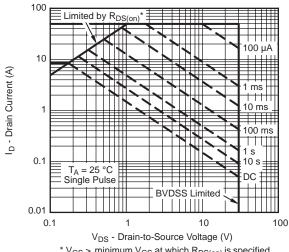






Threshold Voltage

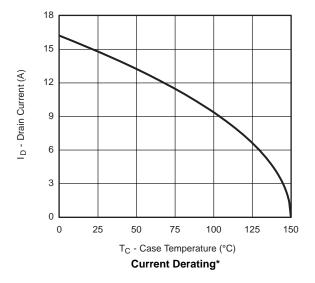
Single Pulse Power, Junction-to-Ambient

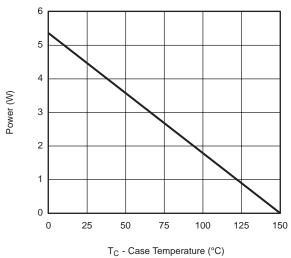


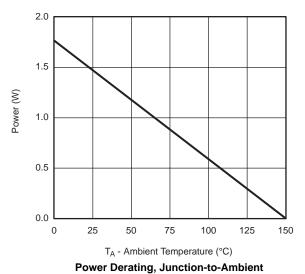
* $V_{GS} > \mbox{minimum } V_{GS}$ at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient









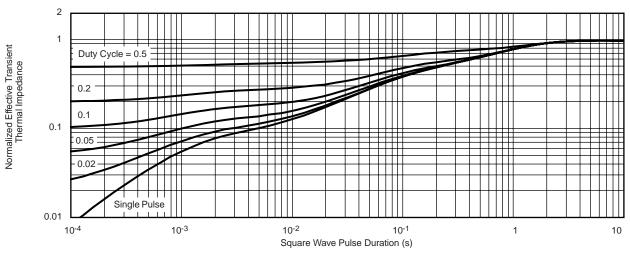
Power Derating, Junction-to-Foot

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





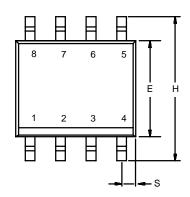
Normalized Thermal Transient Impedance, Junction-to-Ambient

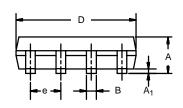


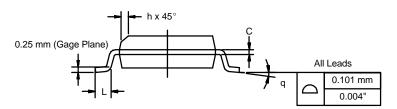
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD







	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sen-06					

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)



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